Diffusion-reaction mechanisms of nitriding species in SiO_2

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We study using first-principles total-energy calculations, diffusion-reaction processes involved in the thermal nitridation of SiO_2. We consider NO, NH, N_2 and atomic N in different charge states as the nitriding species in α-quartz. Our results show that none of neutral species react with the SiO_2 network remaining at interstitial sites. Therefore, they are likely to diffuse through the oxide, incorporating nitrogen at near-interface (Si/SiO_2) regions. Whereas, charged species are trapped by the network, nitriding bulk SiO_2. For the diffusing species, we find that NH and atomic N show increasing diffusivities with temperatures, whereas for NO and N_2 they are relatively constant. This result agree well with the finding of higher N concentration at the Si/SiO_2 interface obtained by thermal processing of SiO_2 in NH_3 as compared with those obtained in N_2O. Finally, we discuss spin-dependent incorporation reaction mechanisms of NH and atomic N with the SiO_2 network.

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I. INTRODUCTION

Nitrided silicon oxide or oxynitride is currently the near-term solution to substitute SiO_2 as the gate insulator material for the ultrathin metal-oxide-semiconductors (MOS) technology. Recent studies have suggested that the performance of oxynitride-based MOS devices depends both on the depth concentration and on the distribution of nitrogen into the gate oxide.[1] According to these studies, the best nitrogen profile for an ultrathin gate oxide would have: (i) a small nitrogen concentration near the SiO_2/Si interface in order to reduce degradations by hot electrons,[2] and (ii) a larger N concentration near the interface between the dielectric and the polycrystalline silicon (poly-Si) gate electrode, in order to minimize dopant diffusion.[3]

The growth of ultrathin oxynitride films depends strongly on the reactant agent (e.g., N_2O, NO, NH_3) and the technique used. Nitrogen can be incorporated into SiO_2 using either thermal oxidation and annealing or chemical and physical deposition methods. Thermal nitridation of SiO_2 in N_2O generally results in a relatively low N concentration at near-interface (Si/SiO_2) region. The nitriding species are originated in the decomposition of the N_2O molecule occurring at typical oxidation temperature, these species being the NO and N_2 molecules.[4,5,6] On the other hand, nitrogen incorporation in SiO_2 can also be performed via annealing in a NH_3 atmosphere, resulting in a relatively high N concentrations into the films.[5] This method provides both near-interface and near-surface nitridation, which suggests different mechanisms for N incorporation or different nitriding species derived from NH_3. The above thermal processing are performed at high temperatures (> 800 C). Plasma nitridation is a promising method for making ultrathin oxynitride at lower temperatures (~ 300–400 C). Higher N concentrations and controlled distribution can be attained with this method,[7] typically using ions and radicals derived from N_2 and NH_3 as nitrogen sources.[8] Additionally, nitridation by energetic particles (N ions) provides high N concentrations much closer to the near-surface region, with little or no nitrogen at the SiO_2/Si interface.[1] Although the nitridation mechanisms to make ultrathin SiO_2 films are well known at the few layer level, less is known about the diffusing mechanism of the nitriding species and their reactions with the oxide at the atomic level.

In this work the energetics and diffusing properties of the SiO_2 thermal nitridation are studied from first-principles total-energy calculations. We have considered the N_2, NH and NO molecules as well as atomic N in different charge states as the nitriding species reacting and diffusing through the SiO_2 network. The outline of the paper is as follows. Section II describes the theoretical procedure. Our results for the interaction of the nitriding species with the SiO_2 network is presented in Sec. III A. The diffusivity of the nitriding species through SiO_2 is presented in Sec. III B. In Sec. III C we discuss the spin-dependent diffusion reactions of NH and atomic N with the SiO_2 network. Finally, in Sec. IV we show our conclusions.

II. THEORETICAL METHOD

Our calculations were performed in the framework of the density functional theory,[9] using a basis set of numerical atomic orbitals as implemented in the SIESTA code.[10] We have used a split-valence double- basis set plus the polarization functions as well as standard norm-conserving pseudopotentials.[11] For the exchange-correlation potential we adopt the generalized gradient approximation.[12] We used a 72-atom α-quartz supercell and the point for the Brillouin zone sampling. The positions of all the atoms in the supercell were relaxed until all the force components were smaller than 0.05 eV/Å. We also consider neutral and singly charged species, where the neutrality of the cell is always maintained by introducing a compensating background charge. Spin-polarization effects are included throughout the calcula-

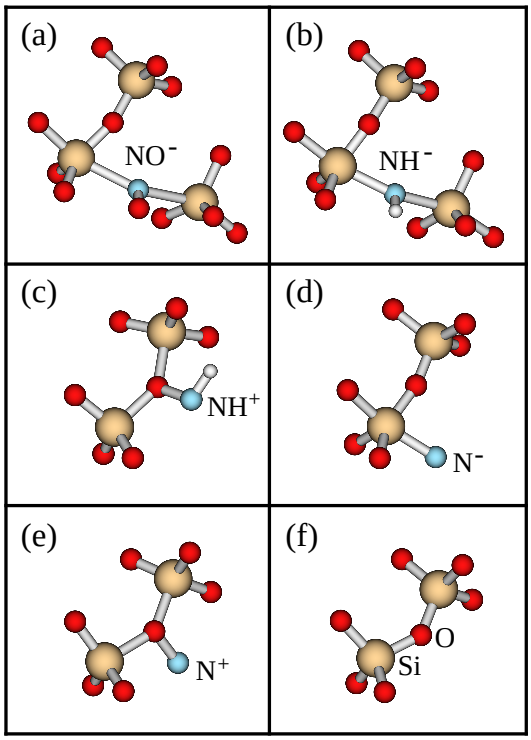

FIG. 1: Local equilibrium geometries for singly charged nitriding species after reacting with the SiO_2 network. (a) negative NO. (b) negative and (c) positive NH, respectively. (d) negative and (e) positive atomic N, respectively. (f) the perfect SiO_2 network.

tion since they are important for the correct description of atomic and molecular reaction processes in SiO_2.[13] We initially study the energetics and structural properties of N_2, NH, NO, and atomic N in the largest interstitial site of -quartz for three different charge states (+;0;). We explore possible reactions that these species may undergo with the network as well as their diffusivities in -quartz.

III. RESULTS AND DISCUSSION

A. Incorporation of nitriding species into the SiO_2 network

Thermal processing of SiO_2 in N_2O and NO atmospheres shows that the NO molecule is the species which diffuses through the oxide, being incorporated at the Si/SiO_2 interface.[6] In our calculations we find that neutral NO and NO^+ do not react with the SiO_2 network, remaining at the interstitial position and being, in this way, able to diffuse through the oxide as experimentally observed. However, NO^- is trapped by the network forming a structure where the N atom of the molecule is bound to two fourfold coordinate Si atoms of SiO_2, as shown in Fig. 1(a). The binding energy of NO^-, calculated as the difference in energy between the bound and the free-interstitial configurations for the same charge state, is found to be 1.3 eV. The Si-N and N-O bond lengths are 2.26 and 1.23 A, respectively, whereas the Si-Si distance decreases by about 6% with respect to the equilibrium SiO_2 structure. For interstitial NO and NO^+ the N-O bond lengths are 1.17 and 1.13 A, respectively.

The NH radical seems to be the most likely diffusing species after thermal dissociation of NH_3 according to the dissociative reactions: $NH_3 \rightarrow NH_2 + H$ 4.5 eV and $NH_2 \rightarrow NH + H$ 3.9 eV. Although NH_2 may be another diffusing species for the interface nitridation, it is a relatively larger molecule and it may suffer additional dissociations at near-surface SiO_2 during thermal processing. According to our results, neutral NH in the gas phase has a spin triplet (S = 1) ground state whereas the singlet (S = 0) states is 2.06 eV higher in energy. However, inside the largest interstitial site of -quartz, this difference in energy between both spin configurations decreases to 1.04 eV, due to the interaction with the crystal field. We find that triplet NH does not react with the SiO_2 network remaining relatively inert at the interstitial sites. However, singlet NH reacts quickly with the oxide forming a structure where the N atom of NH binds to both Si and O atoms of the oxide. This incorporation reaction is highly exothermic with an energy gain of 2.04 eV. In Section III C we discuss the possibility that NH might be incorporated in the SiO_2 network via a triplet-to-singlet spin exchange.

Singly charged NH molecules are highly reactive in the SiO_2 network forming bound configurations as shown in Fig. 1(b) and Fig. 1(c). The binding energies for NH and NH^+ are 3.2 and 2.7 eV, respectively, which suggest that these configurations are very stable favoring a SiO_2 near-surface nitridation. We observe that the NH bound configuration is similar to that previously found for NO. However, the relaxation of the SiO_2 network is larger for the NH bound configuration [see Fig. 1(b)]. Here, both Si-N bond lengths are about 2.1 A, whereas the Si-Si distance decreases by about 14% with respect to the perfect SiO_2 showing a strong lattice relaxation. The N-H bond length is found to be 1.04 A. In the bound NH^+ configuration [Fig. 1(c)], the N atom binds to an O atom of the oxide keeping its bond to the H atom. The O-N and N-H bond lengths are 1.43 and 1.05 A, respectively, forming a O-N-H angle of 103 .

The N_2 molecule is a product of the N_2O gas decomposition at typical oxidation temperatures, being introduced in this way into SiO_2 in thermal processing.[1] N_2 (and atomic N) may also be introduced at lower temperatures by plasma assisted methods.[7] Our results for N_2 in SiO_2 show that this molecule does not react with the oxide being relatively inert for the three charge states considered. Therefore, it may diffuse easily through the oxide reacting with the silicon at the Si/SiO_2 interface or escaping from the lms.

The N atom in free space has a quartet (S = 3/2) ground state. The difference in energy with respect to the doublet (S = 1/2) state is calculated to be 3 eV. However, for a N atom in the largest interstitial site of

-quartz, this energy di erence decreases to 0.76 eV . W e nd that quartet N does not react w ith the SiO_2 network suggesting that it w ould be a di using species. H ow ever, doublet N reacts w ith the oxide being incorporated into SiO_2 network form ing a Si-N-O bond. T his reaction is exotherm ic w ith an energy gain of 0.76 eV . In Section III C, w e discuss the possibility that atom ic N m ight be incorporated in the SiO_2 network via a quartet-to-doublet spin exchange.

Singly charged N atom s are highly reactive in SiO_2. N^+ binds to a fourfold coordinate Si atom form ing an additional Si-N bond of 1.85 A, as shown in Fig. 1(d). The N atom has a binding energy of 2.2 eV . O n the other hand, N^+ binds to an oxygen form ing a O-N bond, as shown in Fig. 1(e). W e nd a O-N bond length of 1.39A w ith a N binding energy of 1.1 eV .

A s a general trend, w e can say that because of the ionic character of SiO_2, charged species are trapped by the network. The positively (negatively) charged NO, NH and N species attach to O (Si) atom s of the oxide, form ing strong bonds, w ith binding energies ranging from 1 to 3 eV . T his suggests a m echanism for the high-density bulk and near-surface nitridation. O n the other hand, the neutral species in their ground-state spin con gurations do not react w ith the SiO_2 network. T herefore, they are able to di use through the oxide.

B. Di usion of nitriding species in SiO_2

W e calculate the di usion coe cient for the neutral species hopping through the larger channel of -quartz, norm al to the c-axis. T o calculate the m igration barriers, w e have follow ed the sam e procedure as described in our previous calculation of the O_2 di usion in -quartz.[14] W e x one atom of the m olecules at several points along the pathway joining neighboring interstitial sites of -quartz w here the distance between them is 5 A . A ll other atom s of the system s are allow ed to relax. O ur results for the total energy variations along this di usion path are shown in Fig. 2. H ere, the zero distance indicates approxim ately the center of the largest interstitial site and the arrow , the place of closest approach to the network. A s a general trend, w e nd an anisotropic energy pro le through the m igration path w hich can be associated to the asym m etry of neighboring interstitial sites. Fig. 2 (a) show s the calculated total-energy variations of di using NO and N_2; w e observe that these species show sim ilar global m inim a and height barriers along the pathway. H ow ever, N_2 exhibits tw o local m inim a not found in the NO pathway, show ing that the interactions between the crystal eld and the m olecular orbitals of the di using species m ay a ect the di usion energy pro le. N evertheless, w e m ust consider that uncertainties are introduced by x ing one atom of the m olecules in order to m ap the di usion energy pro les. For NH and atom ic N w e nd low er-energy barriers and shorter distances between m inim a, as com pared w ith NO and N_2 (see Fig. 2),

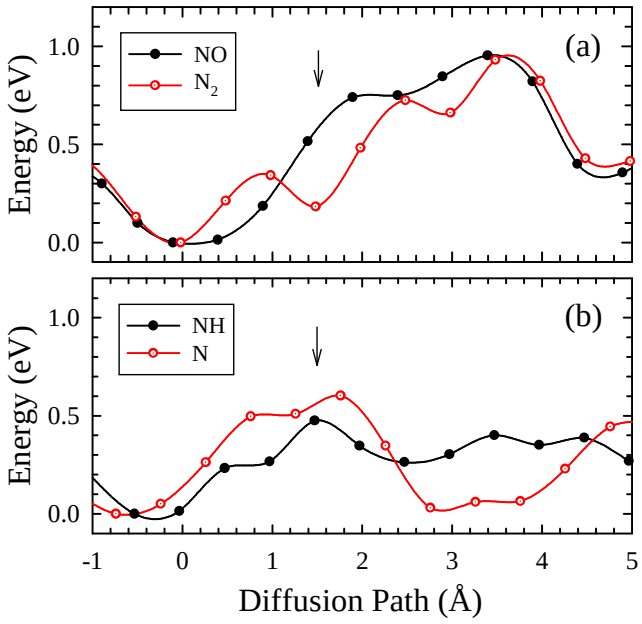

FIG. 2: Total energy variations for the neutral nitriding species di using through a channel norm al to the c-axis of -quartz. (a) for the NO and N_2 m olecules. (b) for the NH m olecule and atom ic N . T he arrow s indicate the point w here the nitriding species pass closer to the SiO_2 network and the zero distance is the center of the largest void in -quartz.

suggesting higher di usivities for these species.

W e estim ate the therm al di usion coe cient or di usivity for the nitriding species using the A rrhenius law , given by

$$D(T) = D_0 \exp(-E_a/kT): \qquad (1)$$

H ere, the prefactor is de ned by $D_0 = l^2 /6$ for a three-dim ensional m igration path, w here l is the hopping distance between m inim a and is the attem pt frequency, kT the B oltzm ann constant tim es the tem perature, and E_a is the highest energy barrier of the m igration path.

is calculated from the energy pro le of each species at the interstitial site (approxim ately the zero distance in Fig. 2), using the harm onic approxim ation, w hereas E_a and l are obtained directly from the sam e gure. Tab. I lists the values of these quantities as w ell as our results

TABLE I: Energy barriers (E_a), hopping distance between m inim a (l) and attem pt frequencies ( ) as obtained from the m igration energy pro les of Fig. 2. D_0 is the calculated prefactor coe cient of the di usivities for each nitriding species.

Species	E_a (eV)	l(A)	(10^{12} sec ^{1})	D_0 (10^{-4} cm ^{2}/sec)
NO	0.95	4.7	2.26	8.32
N_2	0.95	4.8	2.38	9.14
NH	0.48	2.8	3.67	4.79
N	0.60	3.6	3.41	7.37

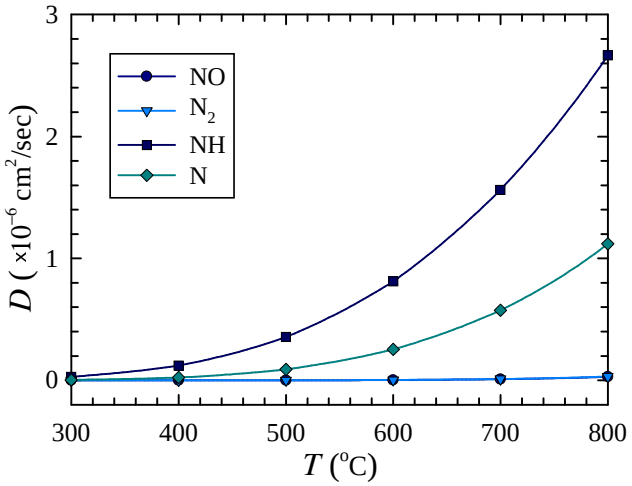

FIG. 3: Calculated diffusivities (D) of the nitriding species in α-quartz as a function of typical plasma assisted and thermal processing temperatures.

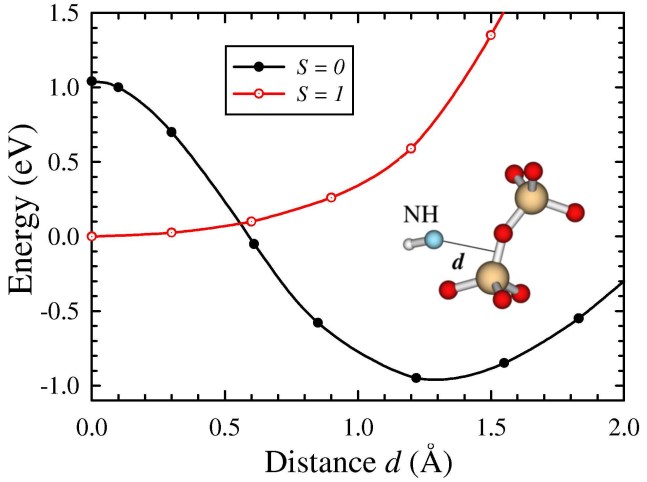

FIG. 4: Triplet ($S = 1$) and singlet ($S = 0$) total-energy curves along the reaction pathway (d in the inset figure) for the NH molecule approaching the SiO_2 network. The zero distance is the equilibrium position of NH in the largest interstitial site of α-quartz where its corresponding total energy is chosen as the zero energy of the system.

for the prefactor of each nitriding species. It is worth pointing out that we have considered a very specific migration pathway through α-quartz. Other pathways may result in different migration barriers and diffusivities. In fact, recent calculations have shown major differences in the diffusivity of atomic hydrogen in different crystalline structures of SiO_2.[15,16] However, we find that our approach is valid to obtain informations on the relative diffusivities of the species under consideration.

Figure 3 shows the diffusivities of the nitriding species in α-quartz as calculated from Eq. 1, for a range of temperatures typically used in thermal and plasma assisted methods. Here we observe that NH and atomic N have the higher diffusivities in α-quartz with increasing temperatures as compared with NO and N_2, which suggest that they would be the best thermally-activated diffusing species in SiO_2 and the most efficient for Si/SiO_2 interface nitridation, as compared with NO and N_2. According to our results, the ratio between NH and NO diffusivities at 800 ^{o}C is estimated to be $D_{NH}=D_{NO}$ ' 90. Assuming that NH and NO are the main diffusing species, our results agree well with the experimental finding of higher N concentrations at the interface obtained by thermal nitridation of SiO_2 in NH_3 as compared with thermal nitridation in NO.[5]

C. Spin-dependent diffusion reactions of NH and N in SiO_2

As mentioned above, NH in the triplet state does not react with the SiO_2 network remaining inert at interstitial sites. However, singlet NH reacts easily with the oxide being incorporated into the network. Because of this spin-dependent reaction of NH with the SiO_2 network, we study the possibility that a diffusing NH may suffer a triplet-to-singlet spin conversion while approaching the oxide, resulting in its incorporation into the network. For this, we compute the potential-energy surface (PES) along a pathway joining the equilibrium position of interstitial NH and a Si-O bond of the SiO_2 network, for both triplet and singlet spin states, as shown in Fig. 4. The triplet PES in the figure is depicted along a direction perpendicular to the diffusion pathway shown in Fig. 2, however, both pathways intercept at the interstitial equilibrium configuration of NH (zero distance in Fig. 4). The probability that the system changes from the triplet to the singlet PES may be estimated by the Landau-Zener theory.[17] This theory has been recently used to describe spin effects in the adsorption of O_2 in the Si(001) surface[18] and the O_2 incorporation reaction in the Si/SiO_2 interface.[13] Considering that the NH is initially in the triplet diffusion PES, and is evolving towards the crossing region with a velocity v, the probability for a conversion to the singlet PES (P_{ts}) may be approximated by

$$P_{ts} = 2\,[1 \quad \exp(-V^2/\hbar v|F_1 \quad F_2|)]; \qquad (2)$$

where V is the triplet-to-singlet spin-orbit matrix element of NH ($X\,^3 \quad ! \quad b^1\,^+$) of 65.1 cm^{-1},[19] F_1 and F_2 are the slopes of the two PES at the crossing point and h is the Planck's constant. v is estimated from the NH center-of-mass thermal velocity at 800 ^{o}C, a typical annealing temperature. F_1 and F_2 are obtained from the triplet and singlet curves at the crossing region (see Fig. 2). Thus, the probability for a triplet-to-singlet conversion is found to be $P_{ts} = 9.3 \quad 10^{-4}$. This means that triplet NH in a single passage through the crossing point has a small probability to change to the singlet PES. However, as the system is thermally activated, many pas-

sages of NH through the crossing point will be performed. In order to quantify the spin-conversion events for NH molecules approaching the SiO_2 network at a given temperature, we estimate the ratio between the rate of NH following the triplet diffusion PES ($_t$) and the rate of NH changing from triplet to singlet PES at the crossing point ($_{ts}$). Assuming that the thermally-activated systems follow the Arrhenius law, the reaction rates can be written as

$$_t = \ _0 \exp(\ E_t/kT) \qquad (3)$$

and

$$_{ts} = \ _0 [\exp(\ E_p/kT)] \ P_{ts}: \qquad (4)$$

Here, $_0$ is the frequency prefactor; E_t is the energy barrier for the triplet diffusion PES obtained from Fig. 2(b) ($E_t = 0.5$ eV) and E_p is the energy difference between the lowest-energy equilibrium configuration of the triplet NH and the crossing point, obtained from Fig. 4 ($E_p = 0.1$ eV). For a temperature of 800 C, we obtain for our calculated P_{ts} that $_t/_{ts} \sim 14$, which indicates that NH will proceed preferentially along the triplet diffusion PES.

As the incorporation of NH into the oxide due to the spin exchange is also likely to occur (an average of one in 14 events), we study three possible thermally-activated diffusion-reaction mechanisms for an incorporated singlet NH at 800 C: (i) NH diffuses along the SiO_2 network by a hopping mechanism. The rate is estimated by Eq. 3, substituting E_t by a calculated hopping energy barrier ($E_h = 2.2$ eV). We find a hopping rate of $_h = \ _0(4.6 \ 10^{11})$. (ii) NH is released from the network following the singlet PES. This reaction rate is estimated by

$$_s = \ _0 [\exp(\ E_s/kT)] \ (1 \ P_{ts}); \qquad (5)$$

where E_s is the singlet PES energy barrier obtained from Fig. 4 ($E_s = 2.0$ eV). We find that $_s = \ _0(4.0 \ 10^{10})$. (iii) NH is released from the network changing from the singlet to the triplet PES at the crossing point. The reaction rate is estimated by Eq. 4, where E_p is now the difference between the energies at the singlet-triplet crossing point and at the incorporated NH equilibrium configuration, obtained from Fig. 4 ($E_p = 1.05$ eV). We find that $_{st} = \ _0(1.1 \ 10^{8})$. According to these results, the most likely diffusion mechanism for an incorporated singlet NH in SiO_2 would be mediated by the reaction (iii), i.e., NH leaves the network changing from the singlet to the triplet PES at the crossing point and then diffuses through SiO_2 as a triplet NH. The two other mechanisms are less likely, as can be verified by the ratios $_{st}/_h \sim 240$ and $_{st}/_s \sim 28$.

Similarly to NH, we find a spin-dependent diffusion reaction for atomic N with the SiO_2 network. According to our results, the N atom in the ground quartet state does not react with the network remaining at interstitial sites, whereas, in the doublet state, the N atom is

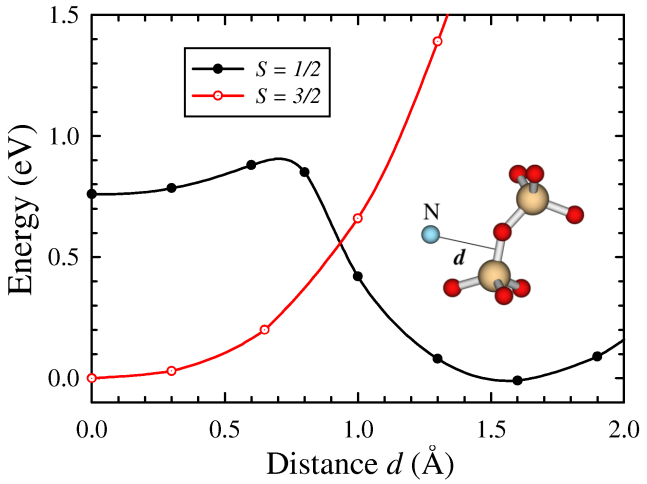

FIG. 5: Doublet (S = 1=2) and quartet (S = 3=2) total-energy curves along the reaction pathway (d in the inset figure) for the N atom approaching the SiO_2 network. The zero distance is the equilibrium position of the N atom in the largest interstitial site of -quartz where its corresponding total energy is chosen as the zero energy of the system.

incorporated between a Si-O bond forming a structure similar to the peroxyl bridge of oxygens[20]. Therefore, we examine the possibility that the N atom, initially in the quartet state, changes the spin configuration to the doublet one, resulting in its incorporation into the oxide. Following the same procedure described above for NH, we compute the quartet and doublet PES for the N atom approaching the SiO_2 network. Our results are shown in Fig. 5. From Eq. 2 we obtain the probability for the spin conversion using for V the quartet-to-doublet spin-orbit matrix element of the N atom ($^4P \ ! \ ^2P$), obtained from spectroscopy data of 13.8 cm^{-1}. Thus, we find a quartet-to-doublet conversion probability $P_{qd} = 1.6 \ 10^{5}$. This probability corresponds to a single passage of the N atom through the crossing point. To estimate the number of spin-conversion events of thermally activated N atoms approaching the SiO_2 network, we calculate the ratio between the rate of N following the quartet diffusion PES ($_q$) and the rate of N changing from doublet to singlet PES at the crossing point ($_{qd}$). To calculate $_q$ we use Eqs. 3 substituting E_t by the energy barrier for the quartet diffusion PES obtained from Fig. 2(b) ($E_q = 0.6$ eV). $_{qd}$ was estimated by Eqs. 4 substituting P_{ts} by P_{qd} and using $E_p = 0.6$ eV, the difference between the energies at the interstitial site and at the quartet-doublet crossing point, obtained from Fig. 5. For a temperature of 800 C, we find that $_q/_{qd} \sim 6 \ 10^{4}$. This results indicates that the N atom will most likely proceed along the quartet PES, i.e., it diffuses through the SiO_2 essentially without reacting with the network.

Although very unlikely, the reaction of a doublet N with the oxide due to the spin exchange may also occur. Again, following the same procedure described for NH, we have three possibilities for the doublet N

diffusion-reaction mechanism once it is incorporated into the oxide: (i) The incorporated N diffuses through the SiO_2 network by a hopping mechanism. From Eq. 3, substituting E_t by the a calculated hopping energy barrier ($E_h = 1.8$ eV), we find a reaction rate of $_h = _0(3.5\ 10^{\ 9})$. (ii) N is released from the network following the doublet PES. From Eq. 5, substituting E_s by the the doublet PES energy barrier, obtained from Fig. 5 ($E_d = 0.9$ eV), and P_{ts} by P_{qd}, we find $_d = _0(5.9\ 10^{\ 5})$. (iii) N is released from the network changing from the doublet to the quartet PES at the crossing point. From Eq. 4, substituting P_{ts} by P_{qd} and using $E_p = 0.6$ eV, the difference between the energies at the interstitial site and at the quartet-doublet crossing point, obtained from Fig. 5, we find $_{dq} = _0(2.4\ 10^{\ 8})$. Therefore, if a N atom is incorporated into the oxide by a quartet-to-doublet spin exchange, a rare event, it will be released from the network following the singlet PES, according to the reaction (ii). However, as the incorporation reaction of the doublet N is exothermic, it will be reincorporated in the network if the timescale for relaxation back to the quartet ground state is long enough. Finally, we find that the other two possible reactions are very unlikely as can be verified by the ratios $_d/_h \sim 1.7\ 10^4$ and $_d/_{dq} \sim 2.5\ 10^3$.

IV. CONCLUSIONS

We conclude that because of the ionic character of SiO_2, charged species are trapped by the network, where positive (negative) species tend to attach to oxygen (silicon) atoms, forming strong bonds with binding energies as high as 3 eV. This suggests a mechanism for the N incorporation in bulk SiO_2 observed in plasma assisted method, which would be associated to charged species surviving the first stages of the incorporation reactions occurring at the surface. Of course, these charged species may also transfer the charge to the network becoming neutral. According to our results, neutral species do not react with the network remaining at interstitial sites, therefore, they would be diffusing species in SiO_2 able to reach the Si/SiO_2 interface.

We estimate the diffusivities of neutral species through α-quartz. Our results show that NH and atomic N have increasing diffusivities with temperature, and the highest one among the nitriding species, suggesting that they would be efficient for near interface nitridation. This result is in good agreement with the finding of high N concentration at the Si/SiO_2 interface obtained by thermal processing in NH_3. On the other hand, NO and N_2 show relatively constant diffusivities in α-quartz for the same range of temperatures. This result is also in good agreement with the finding of relatively low N concentration at the Si/SiO_2 interface obtained by thermal processing in N_2O, which is the main source of NO and N_2 species.

We also study the incorporation reaction of NH and atomic N with the SiO_2 network driven by a spin exchange mechanism. We find that, for a typical annealing temperature (T = 800 C), a NH molecule diffusing through the triplet PES will have, on average, one in forteen possibilities to be incorporated into the network by a triplet-to-singlet conversion. The incorporated singlet NH will most likely return to the triplet PES after an inverse spin conversion. We also find that atomic N may be incorporated into the network by a quartet-to-doublet conversion while diffusing through the quartet PES, however, only an average of one in $6\ 10^4$ events will be successful. If this rare event occurs, the incorporated N will be released from the network following the doublet PES and, subsequently, reincorporated into the network due to the doublet exothermic process. However, this mechanism will be valid if the timescale for the relaxation to the quartet ground state is long enough.

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